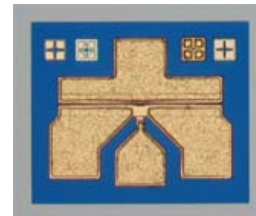


Low Noise and Medium Power GaAs FETs

FEATURES

- Low Noise Figure: NF = 0.5 dB Typical at 12 GHz
- High Associated Gain: Ga = 12 dB Typical at 12 GHz
- High Dynamic Range: 1 dB Compression Power $P_{1dB} = 18.5$ dBm at 12 GHz
- Breakdown Voltage: $BV_{DGO} \geq 9$ V
- $L_g = 0.25 \mu\text{m}$, $W_g = 160 \mu\text{m}$
- All-Gold Metallization for High Reliability
- Tight Vp ranges control
- High RF input power handling capability
- 100 % DC Tested

PHOTO ENLARGEMENT



DESCRIPTION

The TC1101 is a GaAs Pseudomorphic High Electron Mobility Transistor (PHEMT) chip, which has very low noise figure, high associated gain and high dynamic range. The device can be used in circuits up to 30 GHz and suitable for low noise and medium power amplifier applications including a wide range of commercial and military applications. All devices are 100% DC tested to assure consistent quality. All bond pads are gold plated for either thermo-compression or thermo-sonic wire bonding.

ELECTRICAL SPECIFICATIONS ($T_A=25^\circ\text{C}$)

Symbol	Conditions	MIN	TYP	MAX	UNIT
NF	Noise Figure at $V_{DS} = 2$ V, $I_{DS} = 10$ mA, $f = 12$ GHz		0.5	0.7	dB
G_a	Associated Gain at $V_{DS} = 2$ V, $I_{DS} = 10$ mA, $f = 12$ GHz	10	12		dB
P_{1dB}	Output Power at 1dB Gain Compression point, $f = 12$ GHz $V_{DS} = 6$ V, $I_{DS} = 25$ mA	17.5	18.5		dBm
G_L	Linear Power Gain, $f = 12$ GHz $V_{DS} = 6$ V, $I_{DS} = 25$ mA	14	15		dB
I_{DSS}	Saturated Drain-Source Current at $V_{DS} = 2$ V, $V_{GS} = 0$ V		48		mA
g_m	Transconductance at $V_{DS} = 2$ V, $V_{GS} = 0$ V		55		mS
V_p	Pinch-off Voltage at $V_{DS} = 2$ V, $I_D = 0.32$ mA		-1.0*		Volts
BV_{DGO}	Drain-Gate Breakdown Voltage at $I_{DGO} = 0.08$ mA	9	12		Volts
R_{th}	Thermal Resistance		225		$^\circ\text{C}/\text{W}$

Note: * For the tight control of the pinch-off voltage . TC1101's are divided into 3 groups:

(1) **TC1101P0710** : $V_p = -0.7$ V to -1.0 V (2) **TC1101P0811** : $V_p = -0.8$ V to -1.1 V (3) **TC1101P0912** : $V_p = -0.9$ V to -1.2 V

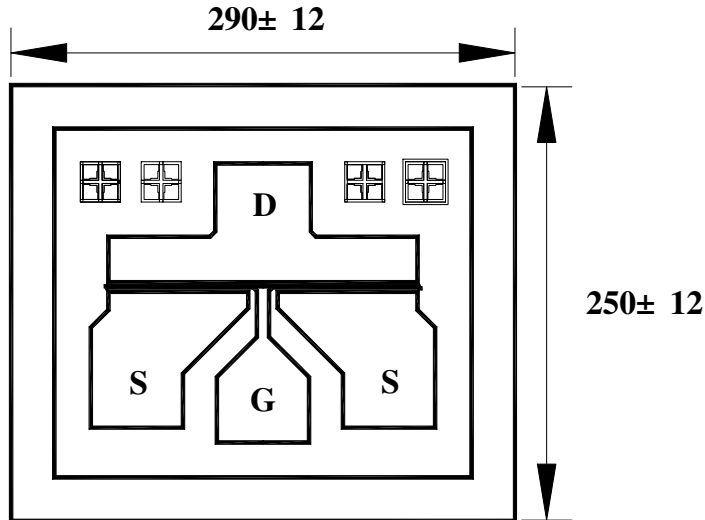
In addition, the customers may specify their requirements.

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$) TYPICAL NOISE PARAMETERS ($T_A=25^\circ\text{C}$)

$V_{DS} = 2$ V, $I_{DS} = 10$ mA

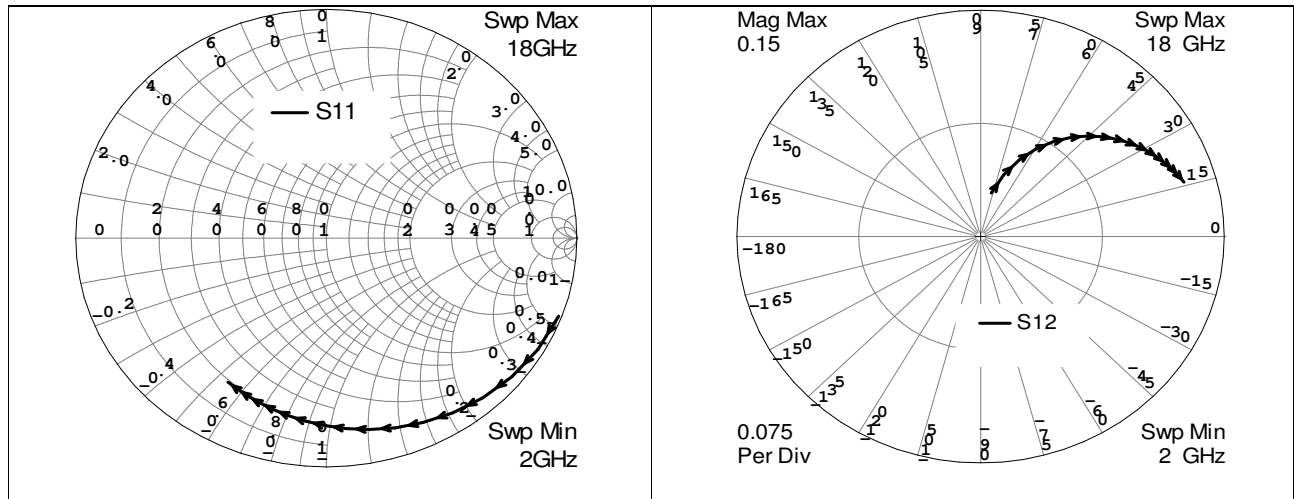
Symbol	Parameter	Rating
V_{DS}	Drain-Source Voltage	7.0 V
V_{GS}	Gate-Source Voltage	-3.0 V
I_{DS}	Drain Current	I_{DSS}
I_{GS}	Gate Current	160 μA
P_{in}	RF Input Power, CW	18 dBm
P_T	Continuous Dissipation	250 mW
T_{CH}	Channel Temperature	175 $^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 $^\circ\text{C}$ to +175 $^\circ\text{C}$

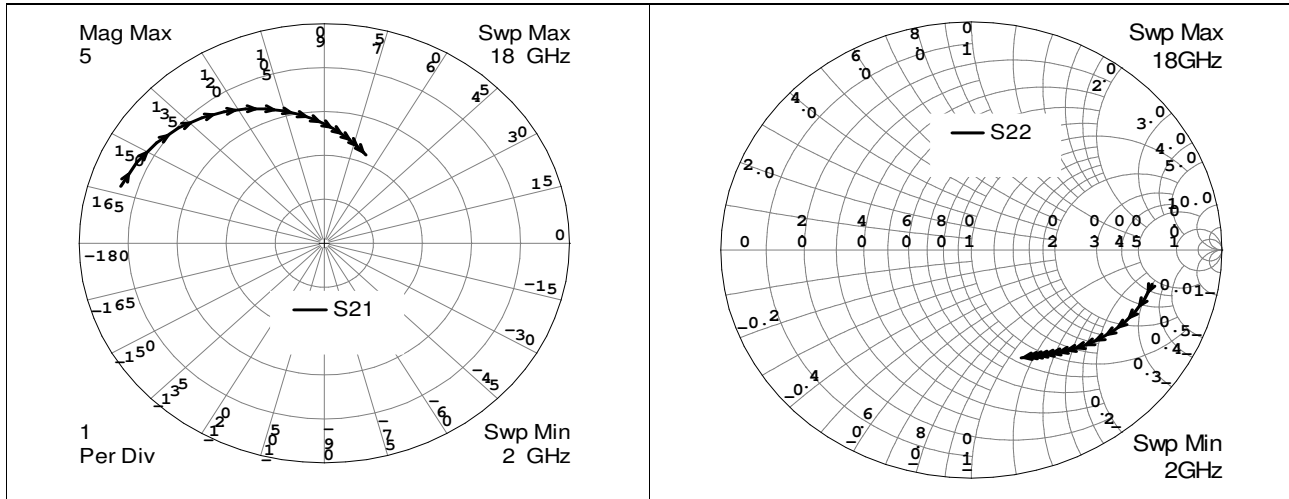
Frequency (GHz)	NF _{ont} (dB)	G _A (dB)	Γ_{opt}		Rn/50
			MAG	ANG	
2	0.38	19.8	0.99	4	0.48
4	0.40	17.5	0.90	9	0.40
6	0.42	15.6	0.82	18	0.37
8	0.45	13.9	0.76	29	0.34
10	0.50	13.1	0.69	43	0.32
12	0.55	12.4	0.63	55	0.30
14	0.64	11.7	0.56	65	0.28
16	0.78	11.1	0.45	76	0.26
18	0.95	10.6	0.34	90	0.24

CHIP DIMENSIONS


Units: Micrometers
 Chip Thickness: 100

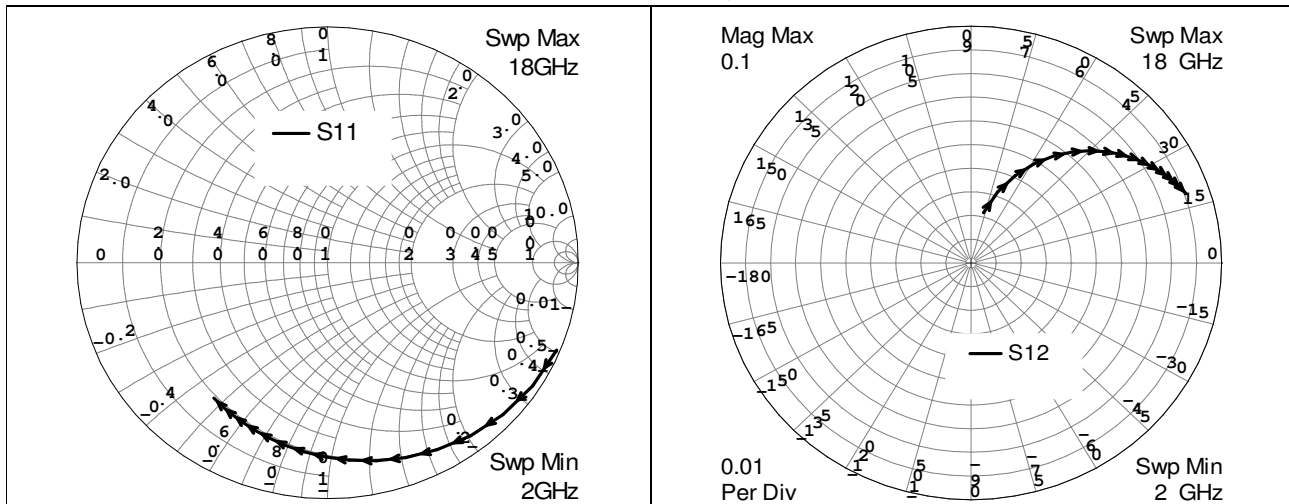
Gate Pad: 55 x 50
 Drain Pad: 55 x 50
 Source Pad: 55 x 60

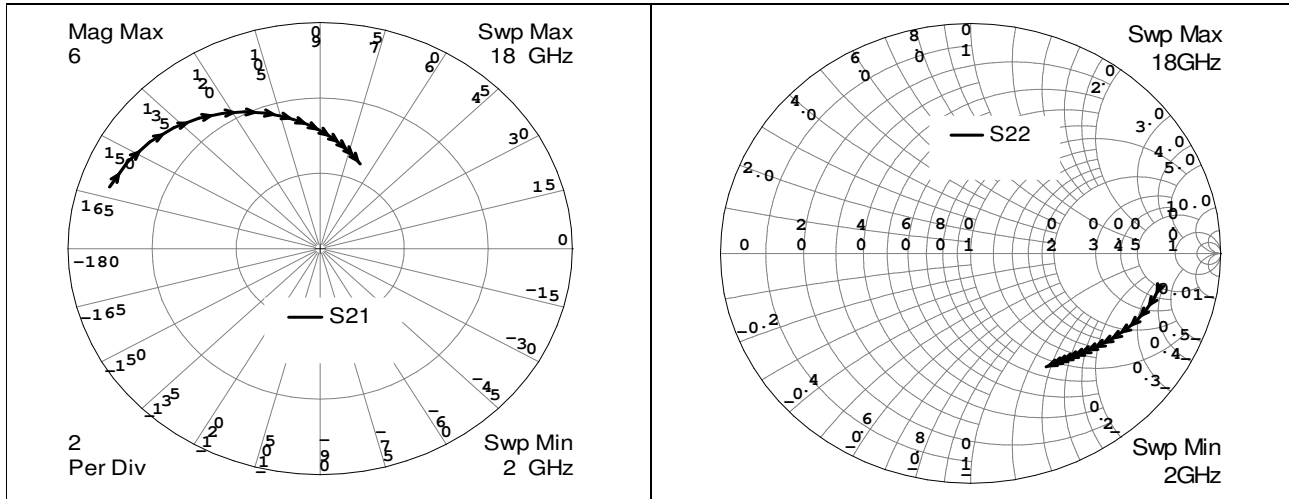
TYPICAL SCATTERING PARAMETERS (T_A=25 °C) V_{DS} = 2 V, I_{DS} = 10 mA




FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2	0.9879	-20.21	4.3485	162.66	0.0296	77.08	0.7367	-11.76
3	0.9740	-29.96	4.2452	154.28	0.0434	70.91	0.7235	-17.37
4	0.9564	-39.31	4.1126	146.20	0.0560	65.04	0.7068	-22.68
5	0.9364	-48.20	3.9594	138.48	0.0674	59.53	0.6877	-27.66
6	0.9152	-56.56	3.7943	131.15	0.0774	54.40	0.6676	-32.28
7	0.8939	-64.40	3.6242	124.22	0.0861	49.66	0.6472	-36.54
8	0.8732	-71.72	3.4546	117.66	0.0937	45.29	0.6276	-40.46
9	0.8536	-78.52	3.2894	111.45	0.1002	41.27	0.6090	-44.06
10	0.8354	-84.84	3.1312	105.57	0.1058	37.57	0.5919	-47.37
11	0.8188	-90.72	2.9813	99.99	0.1106	34.16	0.5764	-50.43
12	0.8037	-96.18	2.8406	94.68	0.1148	31.00	0.5627	-53.28
13	0.7901	-101.25	2.7092	89.60	0.1183	28.08	0.5506	-55.93
14	0.7780	-105.98	2.5868	84.74	0.1214	25.36	0.5402	-58.41
15	0.7671	-110.39	2.4731	80.07	0.1241	22.82	0.5313	-60.76
16	0.7575	-114.51	2.3676	75.57	0.1264	20.44	0.5239	-62.99
17	0.7491	-118.37	2.2697	71.21	0.1284	18.20	0.5179	-65.12
18	0.7416	-121.99	2.1788	66.99	0.1302	16.08	0.5132	-67.16

* The data does not include gate, drain and source bond wires.

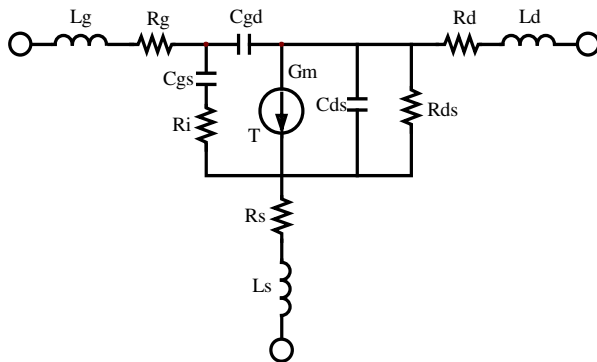
TYPICAL SCATTERING PARAMETERS (T_A=25 °C) V_{DS} = 6 V, I_{DS} = 25 mA




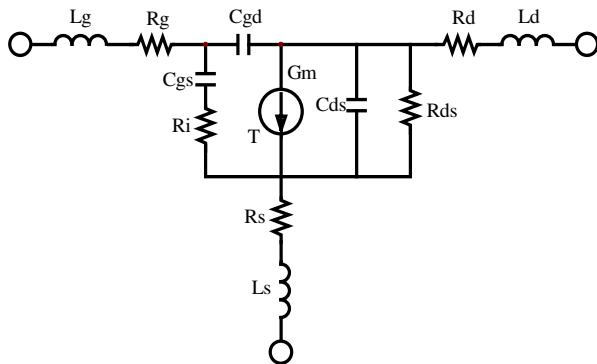
FREQUENCY (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2	0.9861	-22.03	5.2729	161.97	0.0218	76.68	0.7718	-10.24
3	0.9704	-32.59	5.1264	153.31	0.0318	70.37	0.7586	-15.08
4	0.9507	-42.66	4.9406	145.03	0.0408	64.44	0.7422	-19.62
5	0.9288	-52.16	4.7291	137.18	0.0488	58.94	0.7239	-23.82
6	0.9059	-61.05	4.5045	129.78	0.0558	53.89	0.7050	-27.69
7	0.8834	-69.32	4.2765	122.83	0.0618	49.28	0.6865	-31.23
8	0.8618	-76.97	4.0524	116.31	0.0669	45.10	0.6690	-34.49
9	0.8418	-84.05	3.8370	110.19	0.0712	41.30	0.6530	-37.49
10	0.8234	-90.59	3.6330	104.41	0.0749	37.85	0.6386	-40.28
11	0.8068	-96.63	3.4418	98.96	0.0781	34.72	0.6260	-42.90
12	0.7919	-102.23	3.2639	93.79	0.0807	31.86	0.6150	-45.37
13	0.7786	-107.40	3.0990	88.86	0.0830	29.24	0.6057	-47.73
14	0.7668	-112.21	2.9466	84.16	0.0850	26.83	0.5978	-49.99
15	0.7564	-116.69	2.8058	79.65	0.0867	24.60	0.5913	-52.18
16	0.7471	-120.86	2.6758	75.31	0.0882	22.54	0.5861	-54.32
17	0.7389	-124.76	2.5557	71.12	0.0895	20.62	0.5821	-56.41
18	0.7316	-128.41	2.4446	67.06	0.0906	18.82	0.5790	-58.46

*The data does not include gate, drain and source bond wires.

SMALL SIGNAL MODEL, $V_{DS} = 2\text{ V}$, $I_{DS} = 10\text{ mA}$

SCHEMATI

PARAMETERS

Lg	0.047 nH	Rs	1.290 Ohm
Rg	1.460 Ohm	Ls	0.001 nH
Cgs	0.207 pF	Cds	0.068 pF
Ri	3.680 Ohm	Rds	321.5 Ohm
Cgd	0.027 pF	Rd	1.525 Ohm
Gm	54.80 mS	Ld	0.038 nH
T	3.340 psec		

SMALL SIGNAL MODEL, $V_{DS} = 6\text{ V}$, $I_{DS} = 25\text{ mA}$
SCHEMATI

PARAMETERS

Lg	0.047 nH	Rs	1.250 Ohm
Rg	1.460 Ohm	Ls	0.001 nH
Cgs	0.254 pF	Cds	0.067 pF
Ri	5.910 Ohm	Rds	377.8 Ohm
Cgd	0.019 pF	Rd	1.525 Ohm
Gm	66.00 mS	Ld	0.038 nH
T	3.640 psec		

CHIP HANDLING

DIE ATTACHMENT: Conductive epoxy or eutectic die attach is recommended. Eutectic die attach can be accomplished with Au-Sn (80%Au-20%Sn) perform at stage temperature: $290^{\circ}\text{C} \pm 5^{\circ}\text{C}$; Handling Tool: Tweezers; Time: less than 1min.

WIRE BONDING: The recommended wire bond method is thermocompression bonding with 0.7 to 1.0 mil (0.018 to 0.025 mm) gold wire. Stage temperature: 220°C to 250°C ; Bond Tip Temperature: 150°C ; Bond Force: 20 to 30 gms depending on size of wire and Bond Tip Temperature.

HANDLING PRECAUTIONS: The user must operate in a clean, dry environment. Care should be exercised during handling avoid damage to the devices. Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must be less than 300V.